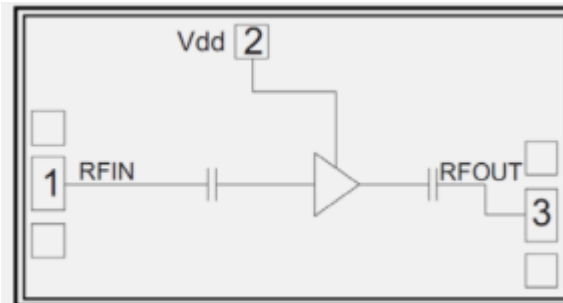


Features

- Single Biasing Voltage (Self Biased)
- Frequency: 6-18GHz
- Small Signal Gain: 10.5dB
- Gain Flatness: $\leq \pm 0.2$ dB
- Noise Figure: 3.2dB, typ.
- P1dB: 19dBm
- Psat: 20dBm
- Power Supply: +5V/75mA
- Input/Output: 50Ω
- Die Size: 1.65 x 1.05 x 0.1 mm

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

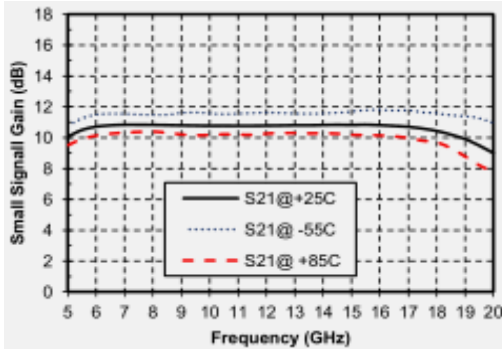
Functional Block Diagram

Electrical Specifications

TA = +25°C, Vd = +5V

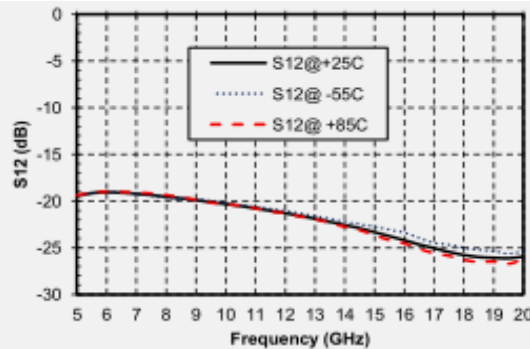
Parameters	Min.	Typ.	Max.	Units
Frequency	6-18			GHz
Small Signal Gain	-	10.5	-	dB
Gain Flatness		±0.2		dB
Noise Figure	3.1	3.2	3.6	dB
Output 1dB Compression (P1dB)	18	19	-	dBm
Saturated Output Power (Psat)	-	20	-	dBm
Input Return Loss	14	19	-	dB
Output Return Loss	14	17	-	dB
Static Current		75		mA



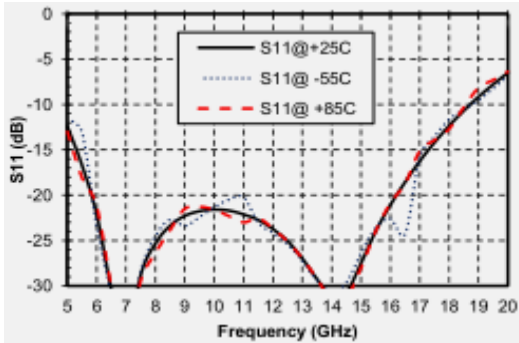
Gain vs. Frequency



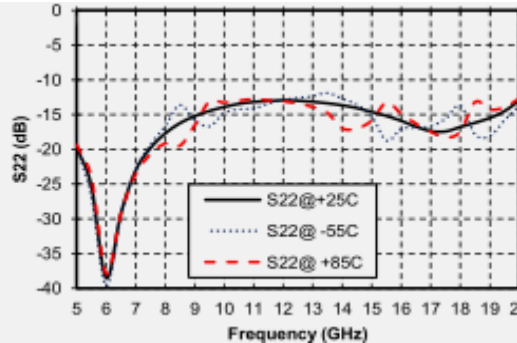
Reverse Isolation & Frequency



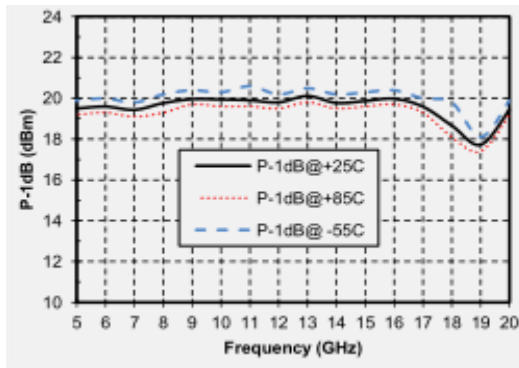
Input Return Loss vs. Frequency



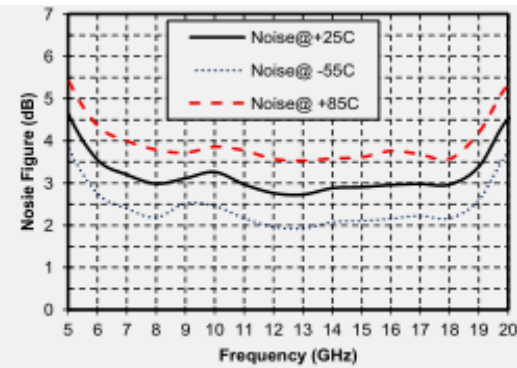
Output Return Loss vs. Frequency



P1dB vs. Frequency

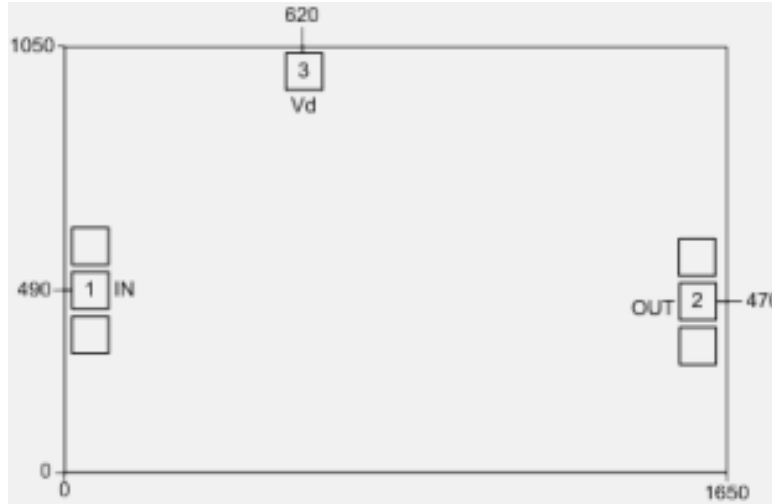


Noise Figure vs. Frequency





Outline Drawing:
All Dimensions in μm

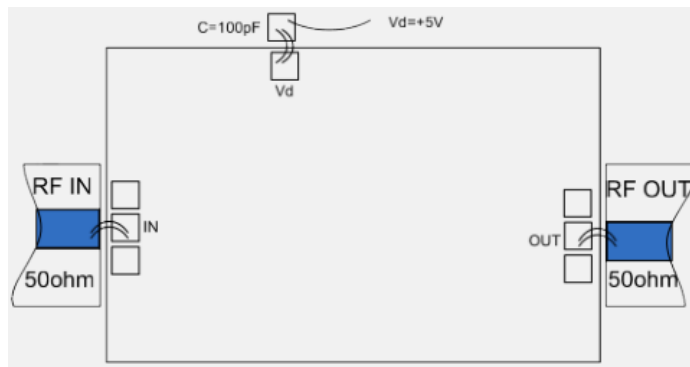


Pad Description

Pad	Function	Description	Equivalent Circuit
1	RF IN	RF signal input terminal; no blocking capacitor required.	
2	RF OUT	RF signal output terminal; no blocking capacitor required.	
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.	
Die bottom	GND	Die bottom must be connected to RF/DC ground.	



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C